# MA27728

### Silicon epitaxial planar type

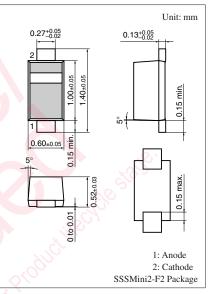
For switching circuits

#### Features

- High-density mounting is possible
- $\bullet$  Low forward voltage  $V_F$  and good wave detection efficiency  $\eta$
- Small temperature coefficient of forward characteristic
- Small reverse current I<sub>R</sub>

| Absolute Maximum Ratings $T_a = 25^{\circ}C$ |                  |             |      |  |  |  |
|--|------------------|-------------|------|--|--|--|
| Parameter                                    | Symbol           | Rating      | Unit |  |  |  |
| Reverse voltage                              | V <sub>R</sub>   | 30          | V    |  |  |  |
| Maximum peak reverse voltage                 | V <sub>RM</sub>  | 30          | V    |  |  |  |
| Forward current                              | I <sub>F</sub>   | 30          | mA   |  |  |  |
| Peak forward current                         | I <sub>FM</sub>  | 150         | mA   |  |  |  |
| Junction temperature                         | Tj               | 125         | °C   |  |  |  |
| Storage temperature                          | T <sub>stg</sub> | -55 to +125 | °C   |  |  |  |

#### Absolute Maximum Ratings $T_a = 25^{\circ}C$



Marking Symbol: R

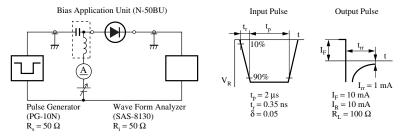
#### Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

| Parameter               | Symbol          | Conditions   | Min | Тур   | Max | Unit |
|-------------------------|-----------------|--|-----|-------|-----|------|
| Forward voltage         | V <sub>F1</sub> | $I_F = 1 \text{ mA}$   | J.  | Jin T | 0.4 | V    |
|                         | V <sub>F2</sub> | $I_F = 30 \text{ mA}$  | 00  | SOL   | 1.0 |      |
| Reverse current         | IR              | $V_R = 30 V$   |     | C.    | 300 | nA   |
| Terminal capacitance    | C <sub>t</sub>  | $V_R = 1 V, f = 1 MHz$   | 2.2 | 1.5   |     | pF   |
| Reverse recovery time * | t <sub>rr</sub> | $I_F = I_R = 10 \text{ mA}$<br>$I_{rr} = 1 \text{ mA}, R_L = 100 \Omega$ |     | 1.0   |     | ns   |
| Detection efficiency    | η               | $V_{IN} = 3 V_{(peak)}, f = 30 MHz$<br>$R_L = 3.9 k\Omega, C_L = 10 pF$  |     | 65    |     | %    |

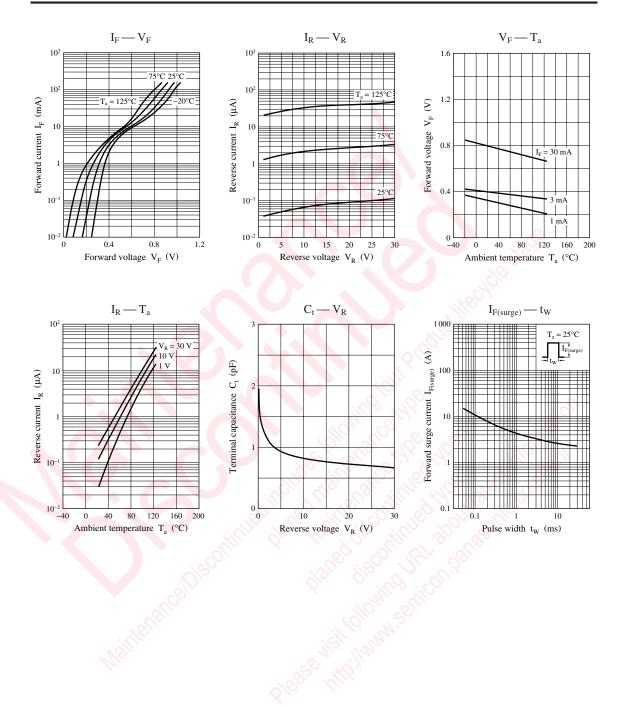
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 measuring methods for diodes.

2. This product is sensitive to electric shock (static electricity, etc.). Due attention must be paid on the charge of a human body and the leakage of current from the operating equipment.

- 3. Absolute frequency of input and output is 2 GHz
- 4. \*: t<sub>rr</sub> measurement circuit



## **Panasonic**



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